DATA SHEET

BFG541
NPN 9 GHz wideband transistor

Product specification

September 1995

NPN 9 GHz wideband transistor BFG541

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

DESCRIPTION

NPN silicon planar epitaxial transistor, intended for wideband applications in the GHz range, such as analog and digital cellular telephones, cordless telephones (CT1, CT2, DECT, etc.), radar detectors, satellite TV tuners (SATV), MATV/CATV amplifiers and repeater amplifiers in fibre-optic systems.

The transistors are mounted in a plastic SOT223 envelope.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

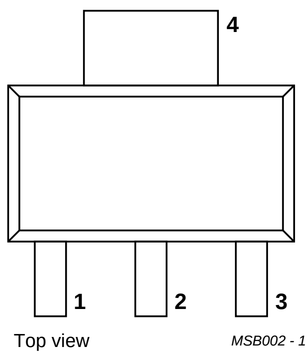


Fig.1 SOT223.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	–	15	V
I_C	DC collector current		–	–	120	mA
P_{tot}	total power dissipation	up to $T_s = 140$ °C; note 1	–	–	650	mW
h_{FE}	DC current gain	$I_C = 40$ mA; $V_{CE} = 8$ V; $T_j = 25$ °C	60	120	250	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 8$ V; f = 1 MHz	–	0.7	–	pF
f_T	transition frequency	$I_C = 40$ mA; $V_{CE} = 8$ V; f = 1 GHz; $T_{amb} = 25$ °C	–	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 40$ mA; $V_{CE} = 8$ V; f = 900 MHz; $T_{amb} = 25$ °C	–	15	–	dB
		$I_C = 40$ mA; $V_{CE} = 8$ V; f = 2 GHz; $T_{amb} = 25$ °C	–	9	–	dB
$\|S_{21}\|^2$	insertion power gain	$I_C = 40$ mA; $V_{CE} = 8$ V; f = 900 MHz; $T_{amb} = 25$ °C	13	14	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 10$ mA; $V_{CE} = 8$ V; f = 900 MHz; $T_{amb} = 25$ °C	–	1.3	1.8	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 40$ mA; $V_{CE} = 8$ V; $R_L = 50\ \Omega$; f = 900 MHz; $T_{amb} = 25$ °C	–	21	–	dBm
ITO	third order intercept point	$I_C = 40$ mA; $V_{CE} = 8$ V; $R_L = 50\ \Omega$; f = 900 MHz; $T_{amb} = 25$ °C	–	34	–	dBm

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	120	mA
P_{tot}	total power dissipation	up to $T_s = 140$ °C; note 1	–	650	mW
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	175	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 140$ °C; note 1	55 K/W

Note

1. T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 8 V	–	–	50	nA
h_{FE}	DC current gain	I_C = 40 mA; V_{CE} = 8 V	60	120	250	
C_e	emitter capacitance	I_C = i_c = 0; V_{EB} = 0.5 V; f = 1 MHz	–	2	–	pF
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = 8 V; f = 1 MHz	–	1	–	pF
C_{re}	feedback capacitance	I_C = 0; V_{CB} = 8 V; f = 1 MHz	–	0.7	–	pF
f_T	transition frequency	I_C = 40 mA; V_{CE} = 8 V; f = 1 GHz; T_{amb} = 25 °C	–	9	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	I_C = 40 mA; V_{CE} = 8 V; f = 900 MHz; T_{amb} = 25 °C	–	15	–	dB
		I_C = 40 mA; V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C	–	9	–	dB
$\|S_{21}\|^2$	insertion power gain	I_c = 40 mA; V_{CE} = 8 V; f = 900 MHz; T_{amb} = 25 °C	13	14	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; I_C = 10 mA; V_{CE} = 8 V; f = 900 MHz; T_{amb} = 25 °C	–	1.3	1.8	dB
		$\Gamma_s = \Gamma_{opt}$; I_C = 40 mA; V_{CE} = 8 V; f = 900 MHz; T_{amb} = 25 °C	–	1.9	2.4	dB
		$\Gamma_s = \Gamma_{opt}$; I_C = 10 mA; V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C	–	2.1	–	dB
P_{L1}	output power at 1 dB gain compression	I_c = 40 mA; V_{CE} = 8 V; R_L = 50 Ω; f = 900 MHz; T_{amb} = 25 °C	–	21	–	dBm
ITO	third order intercept point	note 2	–	34	–	dBm
V_o	output voltage	note 3	–	500	–	mV
d_2	second order intermodulation distortion	note 4	–	–50	–	dB

Notes

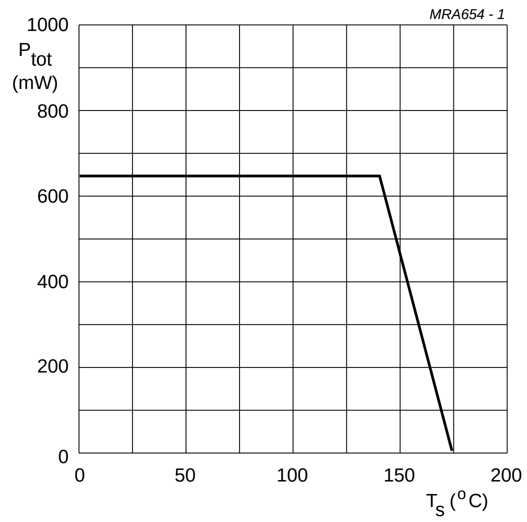
1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10\log\frac{|S_{21}|^2}{(1-|S_{11}|^2)(1-|S_{22}|^2)}\text{ dB.}$$

2. I_C = 40 mA; V_{CE} = 8 V; R_L = 50 Ω; f = 900 MHz; T_{amb} = 25 °C;
   f_p = 900 MHz; f_q = 902 MHz;
   measured at $f_{(2p-q)}$ = 898 MHz and at $f_{(2p-q)}$ = 904 MHz.

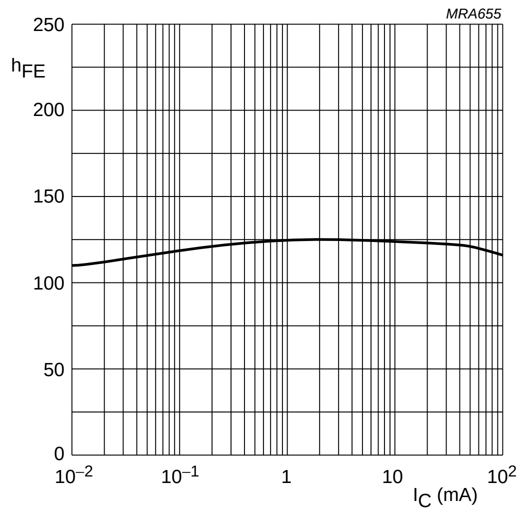
3. d_{im} = –60 dB (DIN 45004B); I_C = 40 mA; V_{CE} = 8 V; $Z_L = Z_s$ = 75 Ω; T_{amb} = 25 °C;
   $V_p = V_o$; $V_q = V_o$ –6 dB; $V_r = V_o$ –6 dB;
   f_p = 795.25 MHz; f_q = 803.25 MHz; f_r = 805.25 MHz;
   measured at $f_{(p+q-r)}$ = 793.25 MHz

4. I_C = 40 mA; V_{CE} = 8 V; V_o = 325 mV; T_{amb} = 25 °C;
   f_p = 250 MHz; f_q = 560 MHz;
   measured at $f_{(p+q)}$ = 810 MHz



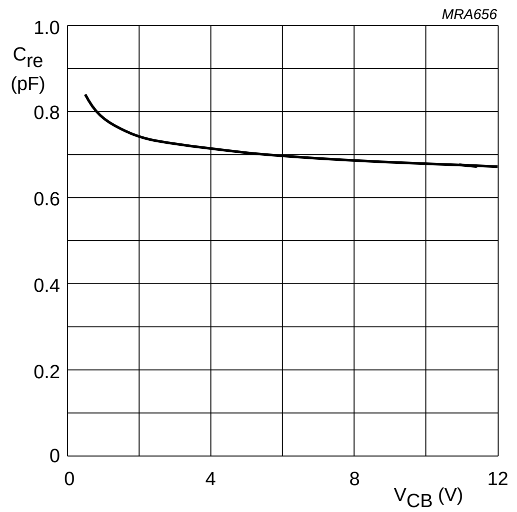
$V_{CE} \leq 10$ V.

Fig.2 Power derating curve.



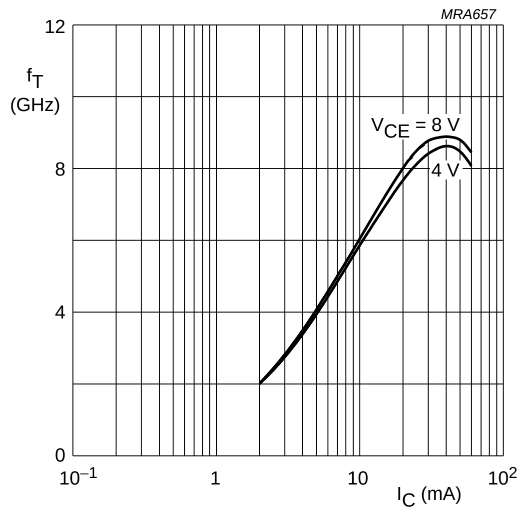
$V_{CE} = 8$ V; $T_j = 25$ °C.

Fig.3 DC current gain as a function of collector current.



$I_C = 0$; f = 1 MHz.

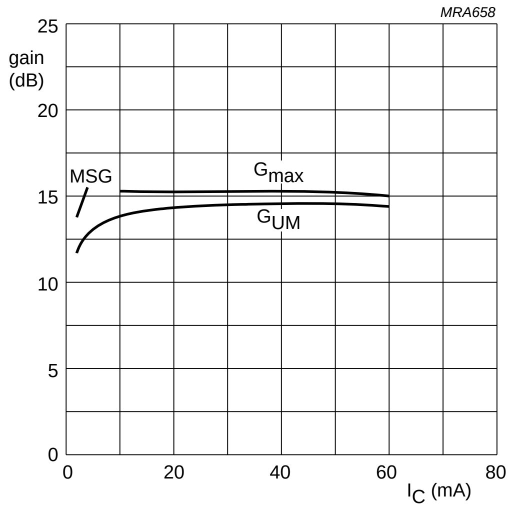
Fig.4 Feedback capacitance as a function of collector-base voltage.



f = 1 GHz; $T_{amb} = 25$ °C.

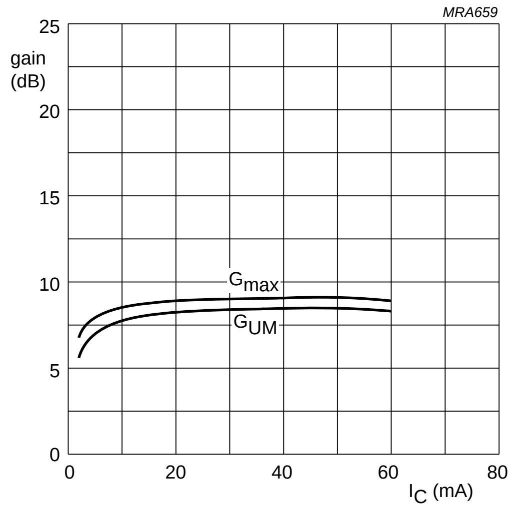
Fig.5 Transition frequency as a function of collector current.

In Figs 6 to 9, G_{UM} = maximum power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



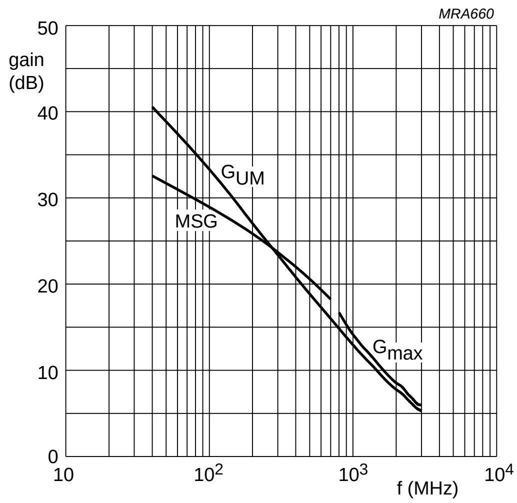
V_{CE} = 8 V; f = 900 MHz.

Fig.6 Gain as a function of collector current.



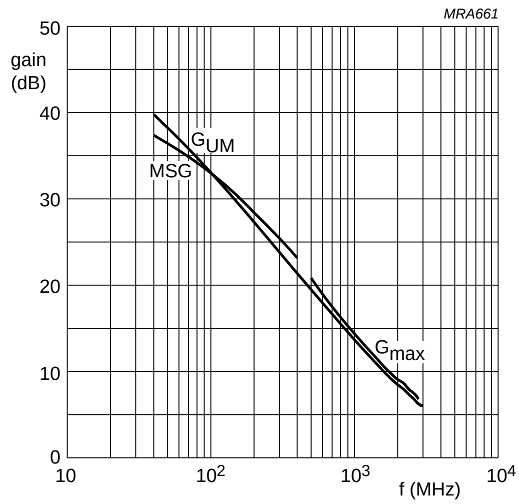
V_{CE} = 8 V; f = 2 GHz.

Fig.7 Gain as a function of collector current.



I_C = 10 mA; V_{CE} = 8 V.

Fig.8 Gain as a function of frequency.



I_C = 40 mA; V_{CE} = 8 V.

Fig.9 Gain as a function of frequency.

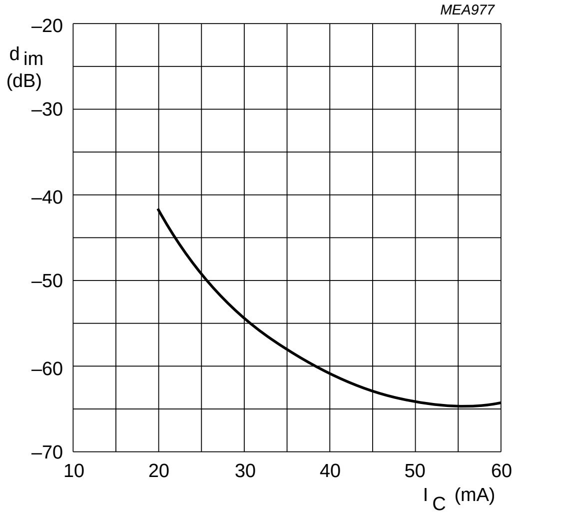


Fig.10 Intermodulation distortion as a function of collector current.

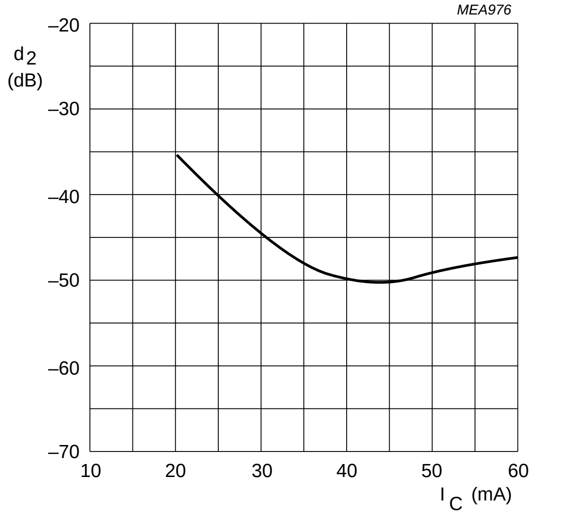
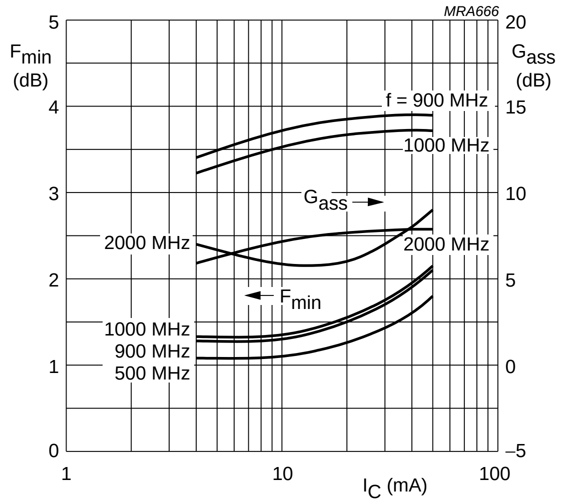
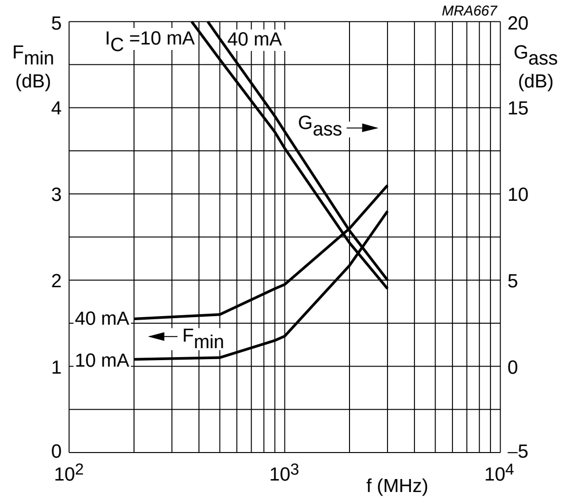


Fig.11 Second order intermodulation distortion as a function of collector current.



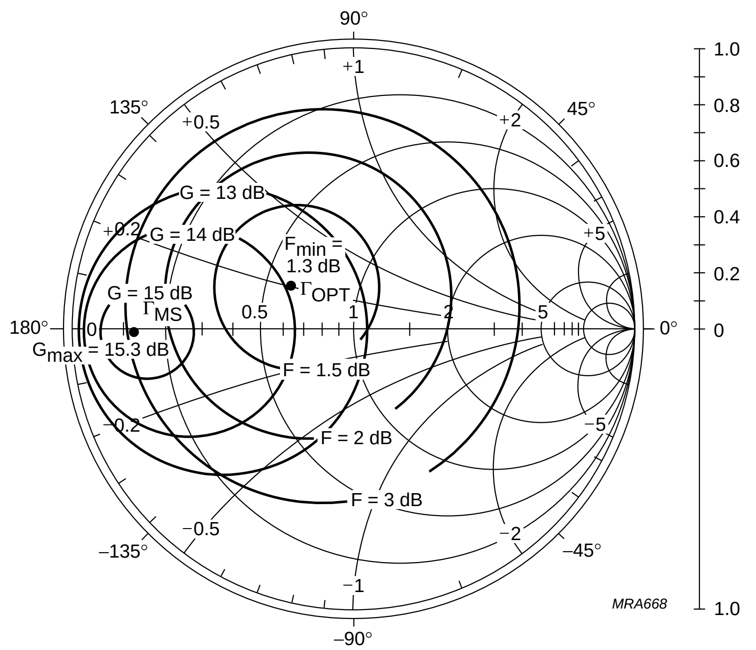
V_{CE} = 8 V.

Fig.12 Minimum noise figure and associated available gain as functions of collector current.



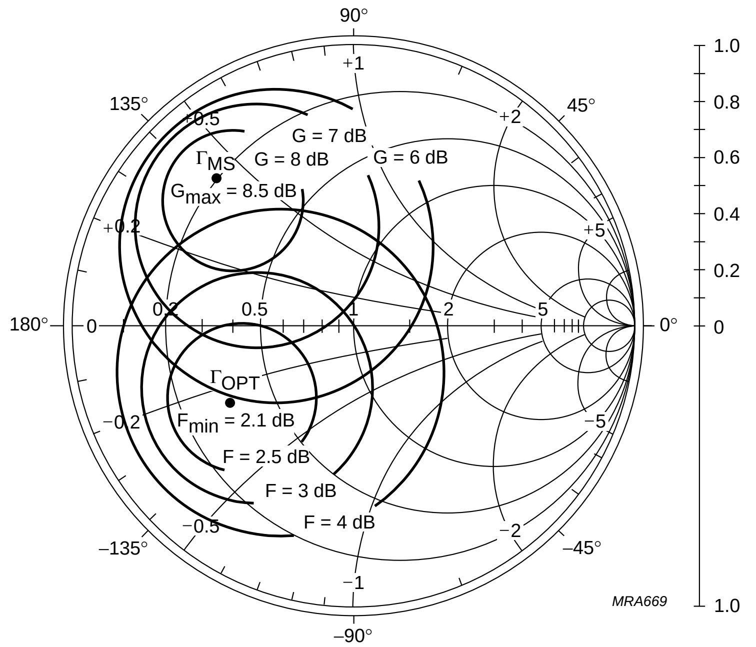
V_{CE} = 8 V.

Fig.13 Minimum noise figure and associated available gain as functions of frequency.



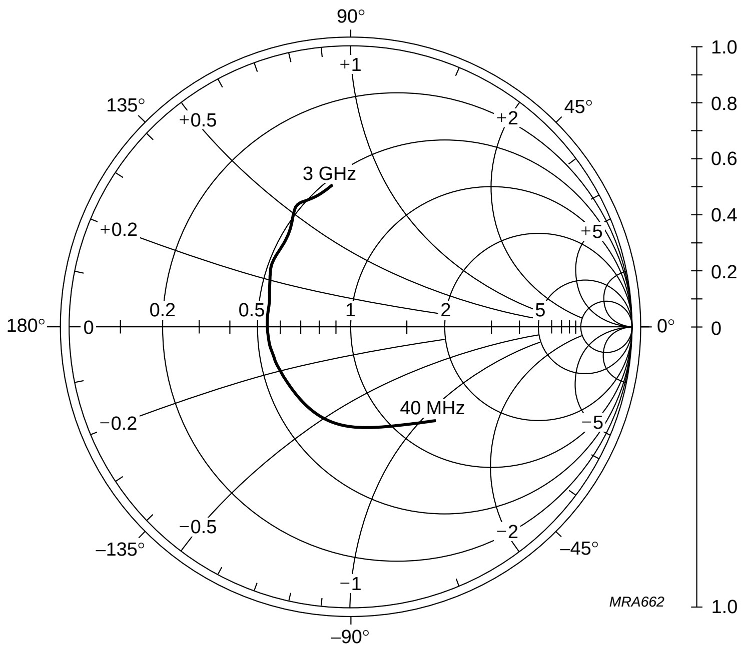
I_C = 10 mA; V_{CE} = 8 V;
Z_o = 50 Ω; f = 900 MHz.

Fig.14 Noise circle figure.



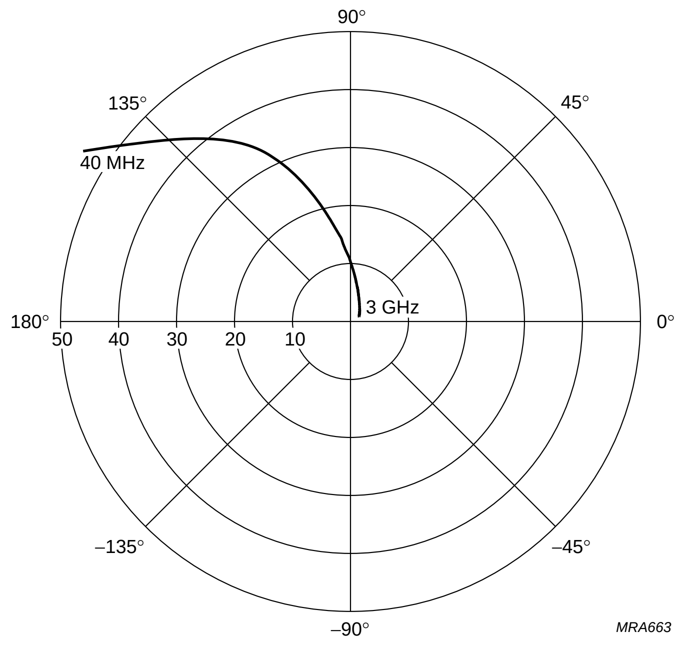
I_C = 10 mA; V_{CE} = 8 V;
Z_o = 50 Ω; f = 2 GHz.

Fig.15 Noise circle figure.



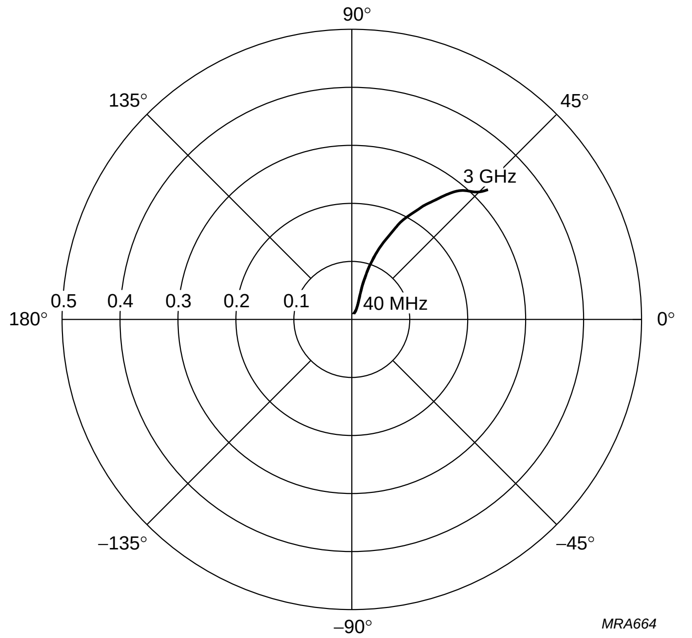
I_C = 40 mA; V_{CE} = 8 V.
Z_o = 50 Ω.

Fig.16 Common emitter input reflection coefficient (S_{11}).



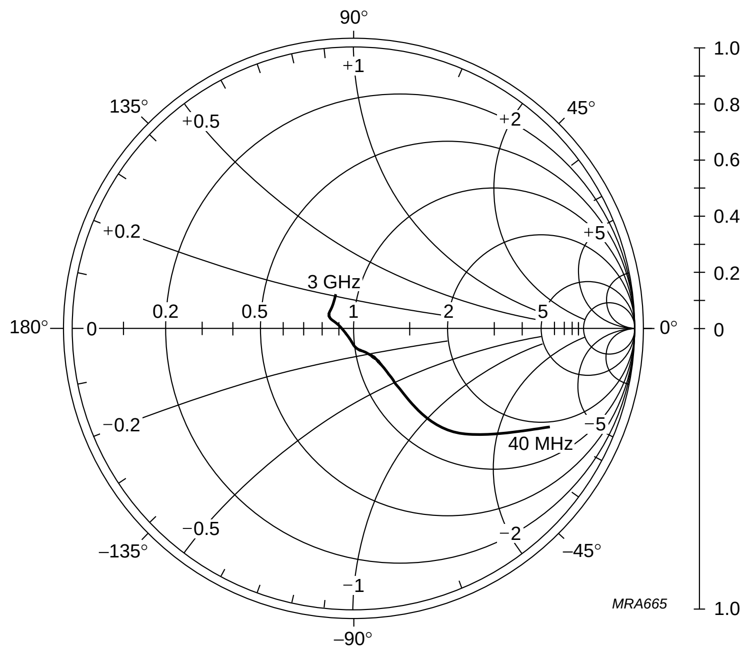
I_C = 40 mA; V_{CE} = 8 V.

Fig.17 Common emitter forward transmission coefficient (S_{21}).



I_C = 40 mA; V_{CE} = 8 V.

Fig.18 Common emitter reverse transmission coefficient (S_{12}).

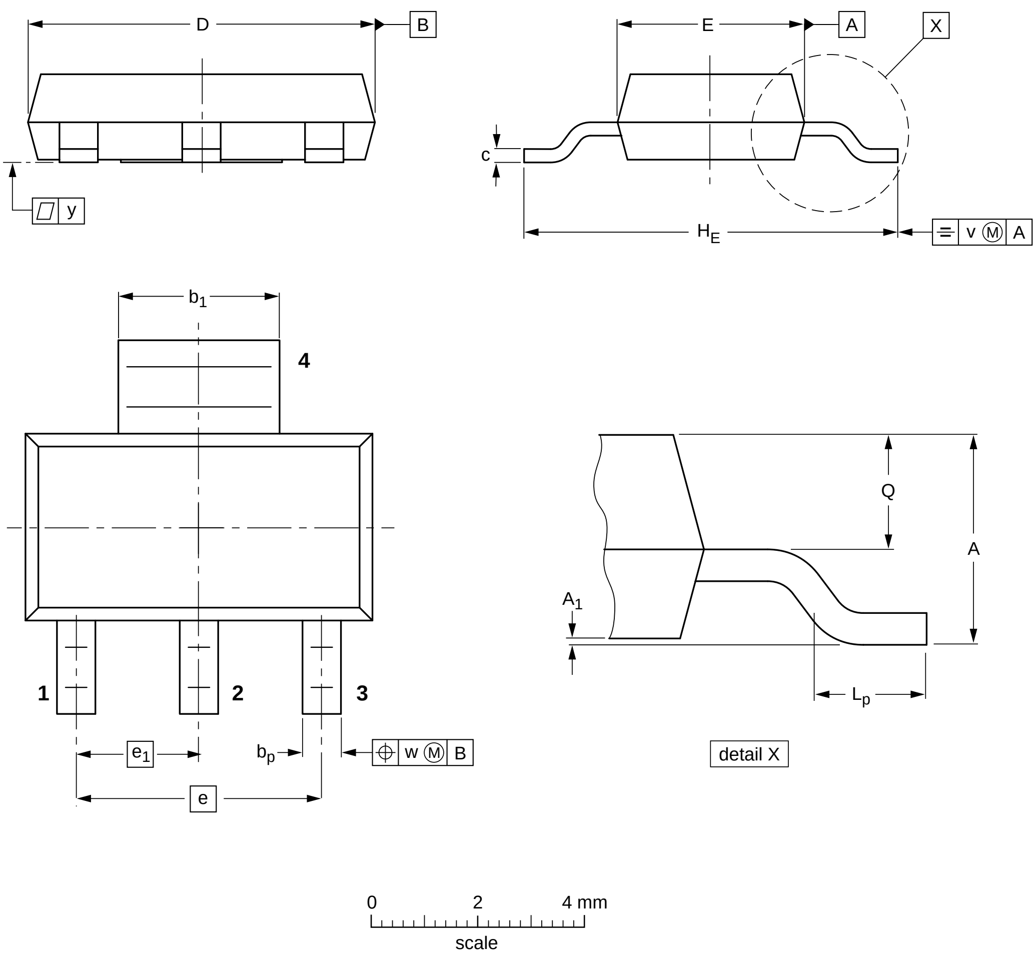


I_C = 40 mA; V_{CE} = 8 V.
Z_o = 50 Ω.

Fig.19 Common emitter output reflection coefficient (S_{22}).

PACKAGE OUTLINE

Plastic surface-mounted package with increased heatsink; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			~~04-11-10~~ 06-03-16

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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